PNP General Purpose Transistor

The MMBT2907AM3T5G device is a spin-off of our popular SOT-23 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-723 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- Reduces Board Space
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-60	Vdc
Collector - Base Voltage	V _{CBO}	-60	Vdc
Emitter – Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	I _C	-600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	265 2.1	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	640 5.1	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	195	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

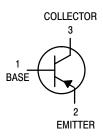
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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3 2

DIAGRAM





MARKING

AC M Specific Device CodeDate Code

ORDERING INFORMATION

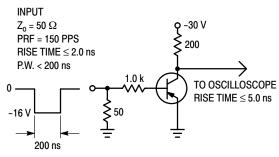
Device	Package	Shipping [†]
MMBT2907AM3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel
NSVMMBT2907AM3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS				1	
Collector–Emitter Breakdown Voltage (Note 3) (I _C = -10 mAdc, I _B = 0)			-60	_	Vdc
Collector – Base Breakdown Voltage (I _C = –10 µAdc, I _E = 0)			-60	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = -10 \mu Adc, I_C = 0$)			-5.0	_	Vdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)		I _{CEX}	_	-50	nAdc
Collector Cutoff Current ($V_{CB} = -50 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = -50 \text{ Vdc}$, $I_E = 0$, $T_A = 125^{\circ}\text{C}$)			_ _	-0.010 -10	μAdc
Base Cutoff Current ($V_{CE} = -30 \text{ Vdc}$, $V_{EB(off)} = -0.5 \text{ Vdc}$)			-	-50	nAdc
ON CHARACTERISTICS				•	
DC Current Gain $ \begin{aligned} &(I_C = -0.1 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -1.0 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -10 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -150 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -500 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \end{aligned} $		h _{FE}	75 100 100 100 50	- - - 300 -	-
Collector – Emitter Saturation Voltage (Note 3) ($I_C = -150$ mAdc, $I_B = -15$ mAdc) (Note 3) ($I_C = -500$ mAdc, $I_B = -50$ mAdc)		V _{CE(sat)}	- -	-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (Note 3) (I _C = -150 mAdc, I _B = -15 mAdc) (I _C = -500 mAdc, I _B = -50 mAdc)			-	-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (Notes 3, 4) (I _C = –50 mAdc, V _{CE} = –20 Vdc, f = 100 MHz)		f _T	200	-	MHz
Output Capacitance ($V_{CB} = -10 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)			-	8.0	pF
Input Capacitance $(V_{EB} = -2.0 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$			_	30	
SWITCHING CHARACTERISTICS					•
Turn-On Time		t _{on}	-	45	
Delay Time	$(V_{CC} = -30 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = -15 \text{ mAdc})$	t _d	_	10	1
Rise Time	10 III (do)	t _r	_	40	1
Turn-Off Time		t _{off}	_	100	ns
Storage Time	$(V_{CC} = -6.0 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = I_{B2} = -15 \text{ mAdc})$		_	80	1
Fall Time		t _f	_	30	

- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%. 4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.





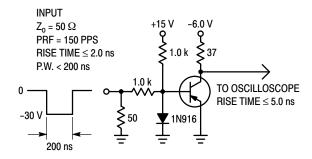


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

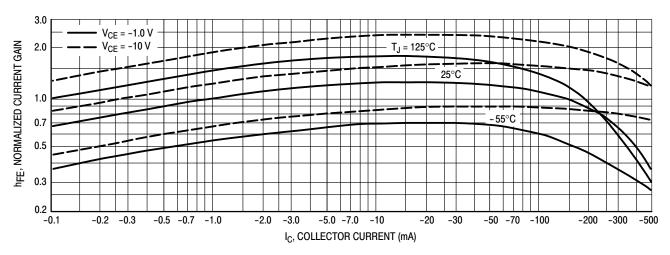


Figure 3. DC Current Gain

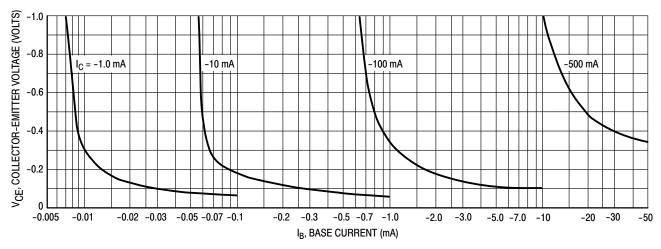


Figure 4. Collector Saturation Region

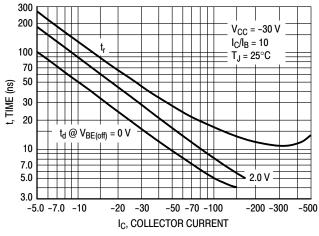


Figure 5. Turn-On Time

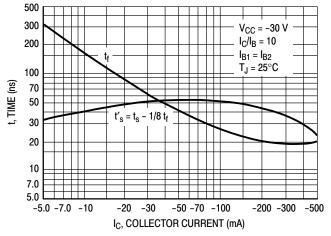
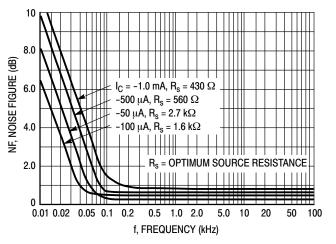


Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

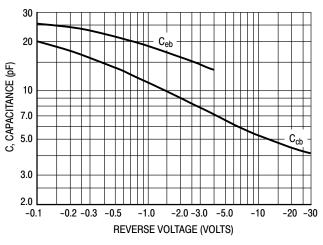
 V_{CE} = 10 Vdc, T_A = 25°C



8.0 NF, NOISE FIGURE (dB) 6.0 $I_C = -50 \mu A$ -100 μA -500 μA 4.0 1.0 mA 2.0 100 200 2.0 k 5.0 k 10 k 50 k 50 1.0 k 20 k R_s, SOURCE RESISTANCE (OHMS)

Figure 7. Frequency Effects

Figure 8. Source Resistance Effects



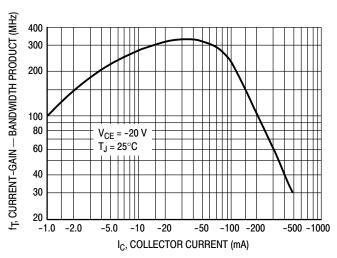
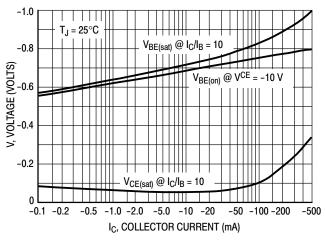


Figure 9. Capacitances

Figure 10. Current-Gain - Bandwidth Product



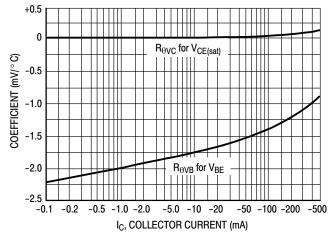


Figure 11. "On" Voltage

Figure 12. Temperature Coefficients



SOT-723 CASE 631AA-01 ISSUE D

DATE 10 AUG 2009

NOTES:

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
С	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
е	0.40 BSC		
ΗE	1.15	1.20	1.25
L	0.29 REF		
12	0.15	0.20	0.25

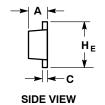
L2 0.15 0.20 0.25 **GENERIC** MARKING DIAGRAM*

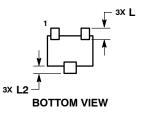


= Specific Device Code XX Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

-X-2X b ⊕ 0.08 X Y **TOP VIEW**

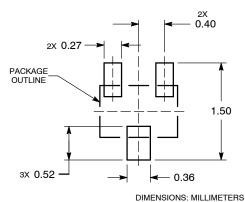




STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SOT-723		PAGE 1 OF 1

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